

Amendments to the Specification

Paragraph at page 7, line 23 to page 8, line 4:

A further problem with polymerization in a fluorine-based etch is that the polymer formation may depend critically upon the processing conditions. It may be possible to achieve high selectivity with processing conditions produced by one set of processing parameters, but very small variations in those conditions may be enough to either substantially reduce the selectivity on one hand or to produce etch stop on the other. Either result is unacceptable in a commercial process. Such variations can occur in at least two ways. The conditions at the middle of the wafer may vary from those at the center. Furthermore, the conditions may change over time on the order of minutes as the chamber warms up or on the order of days as the equipment ages or as chamber parts are replaced. It is felt that hardware can be controlled to no better than ± 5 or 6%, and a safety margin of 3 to 6 is desired. Mass flow controllers are difficult to control to less than ± 1 sccm (standard cubic centimeter per minute) of gas flow so gas flows of any constituent gas of only a few sccm are prone to large percentage variations.